优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_C = +25°C$
-30V	28mΩ @ V_{GS} = -10V	-21A
	38mΩ @ V_{GS} = -4.5V	-18A

Features

- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching – Ensures More Reliability

Description and Applications

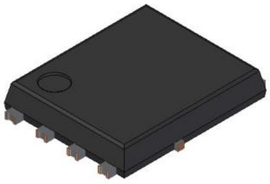
This new generation MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in power management and load switch.

- Backlighting
- Power Management Functions
- DC-DC Converters

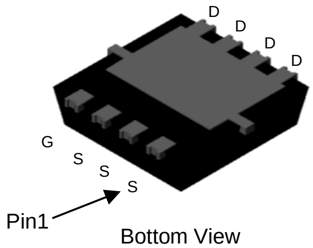
Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⓔ3
- Weight: 0.097 grams (Approximate)

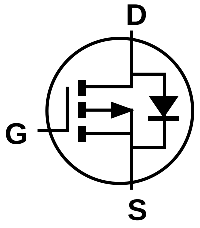
PowerDI5060-8 (SWP) (Type UX)



Top View



Bottom View



Equivalent Circuit

Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 6)	Steady State	T_C = +25°C T_C = +100°C	I_D	-21 -17	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-20	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I_{DM}	-70	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)			I_{SM}	-70	A
Avalanche Current, L = 0.1mH			I_{AS}	-22	A
Avalanche Energy, L = 0.1mH			E_{AS}	24	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.28	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	100	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	2.1	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	60	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-1.3	-2.4	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	18	28	mΩ	V_{GS} = -10V, I_D = -7A
		—	28	38		V_{GS} = -4.5V, I_D = -6.2A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -2.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1421	—	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	147	—		
Reverse Transfer Capacitance	C_{rss}	—	110	—		
Gate Resistance	R_g	—	15	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	22	—	nC	V_{DS} = -15V, I_D = -7A
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	11	—		
Gate-Source Charge	Q_{gs}	—	3.5	—		
Gate-Drain Charge	Q_{gd}	—	4.7	—		
Turn-On Delay Time	$t_{D(ON)}$	—	9.7	—	ns	V_{DD} = -15V, V_{GS} = -10V, I_D = -7A, R_G = 6Ω
Turn-On Rise Time	t_R	—	17.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	60.5	—		
Turn-Off Fall Time	t_F	—	40.4	—		
Body Diode Reverse Recovery Time	t_{RR}	—	10.3	—	ns	I_S = -7A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	3.1	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

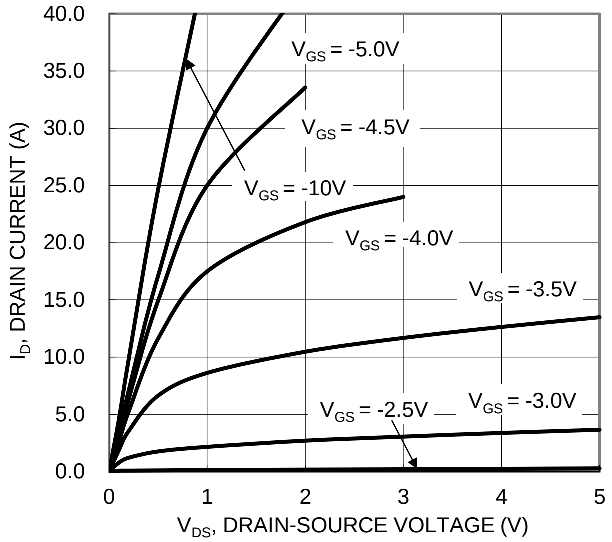


Figure 1. Typical Output Characteristic

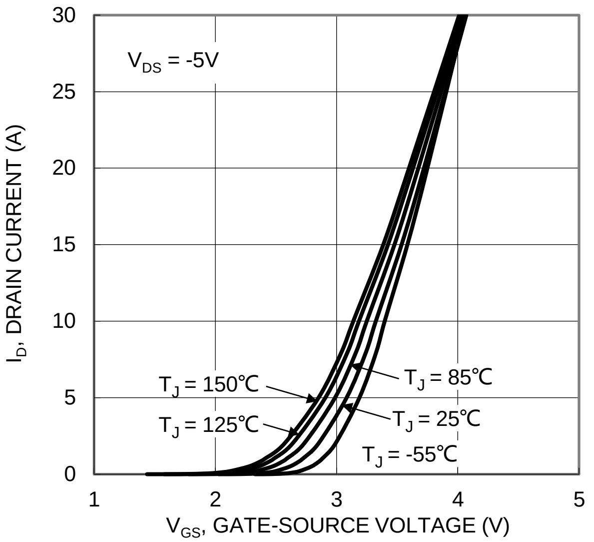


Figure 2. Typical Transfer Characteristic

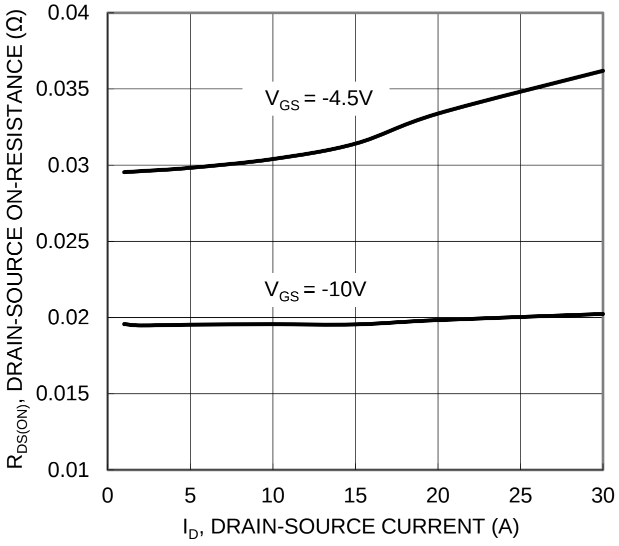


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

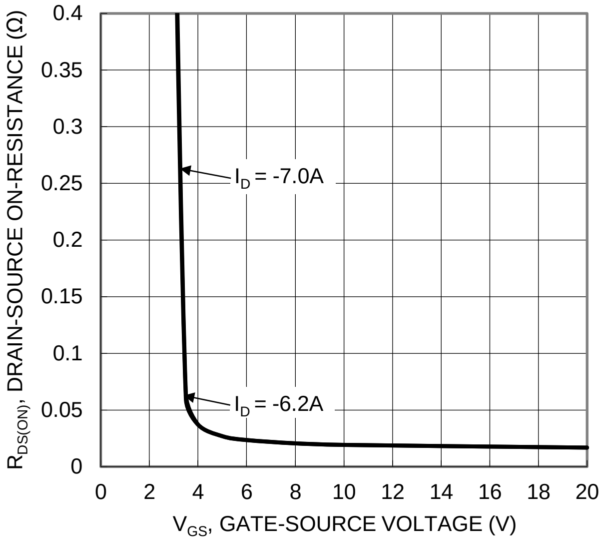


Figure 4. Typical Transfer Characteristic

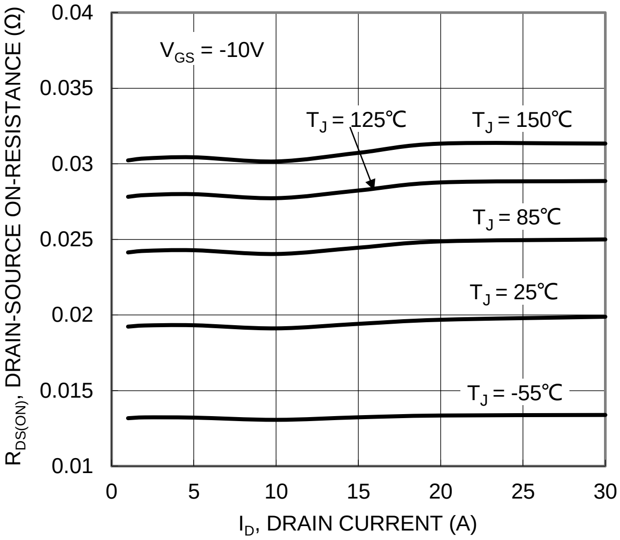


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

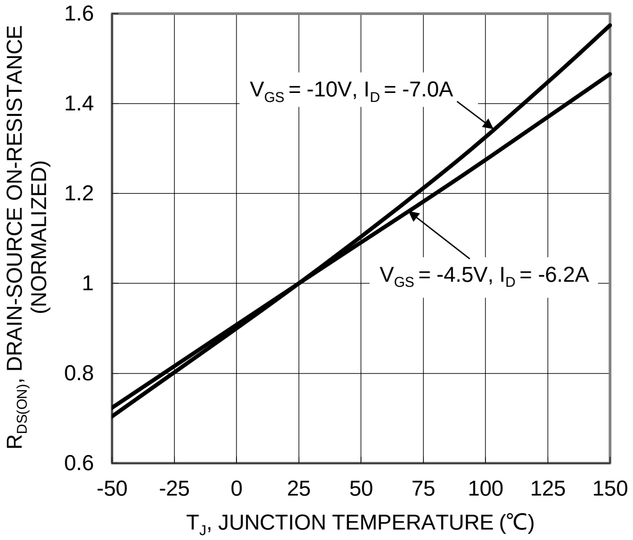


Figure 6. On-Resistance Variation with Junction Temperature

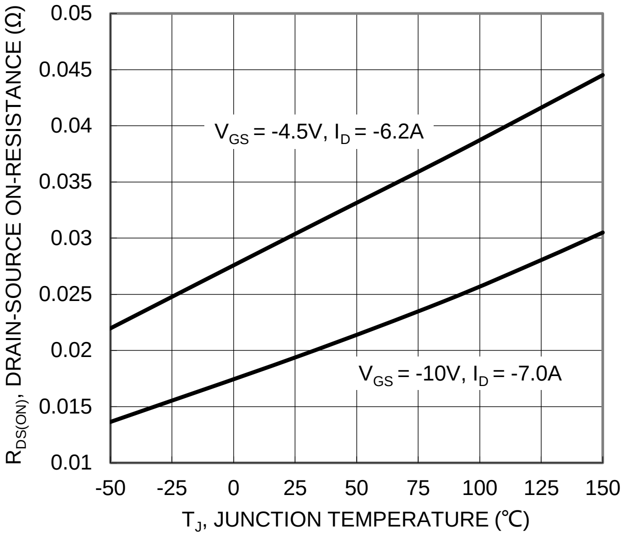


Figure 7. On-Resistance Variation with Junction Temperature

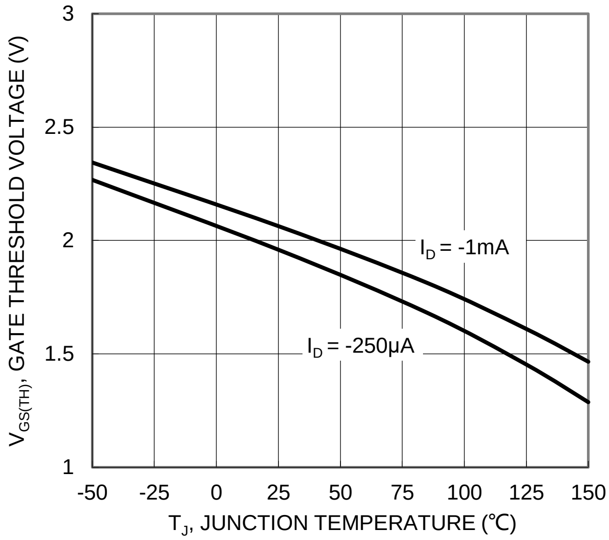


Figure 8. Gate Threshold Variation vs. Junction Temperature

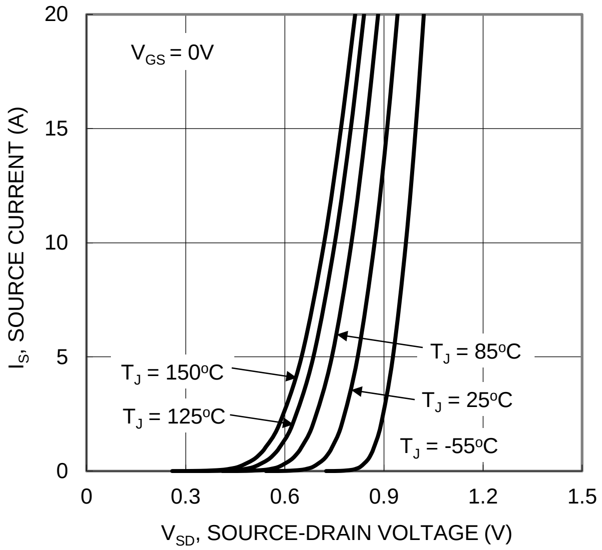


Figure 9. Diode Forward Voltage vs. Current

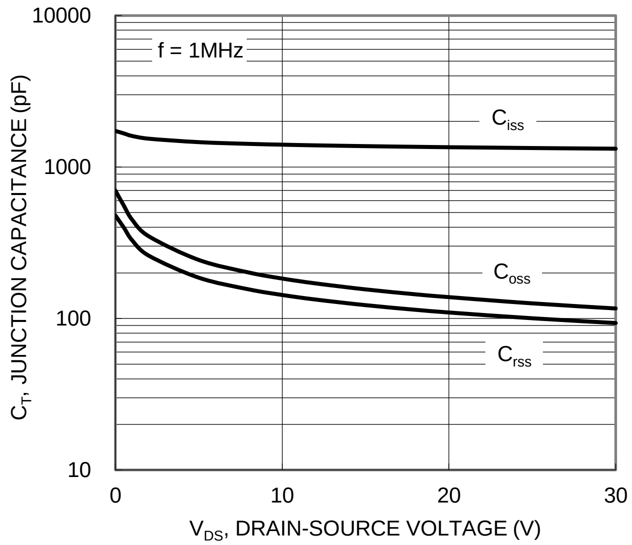


Figure 10. Typical Junction Capacitance

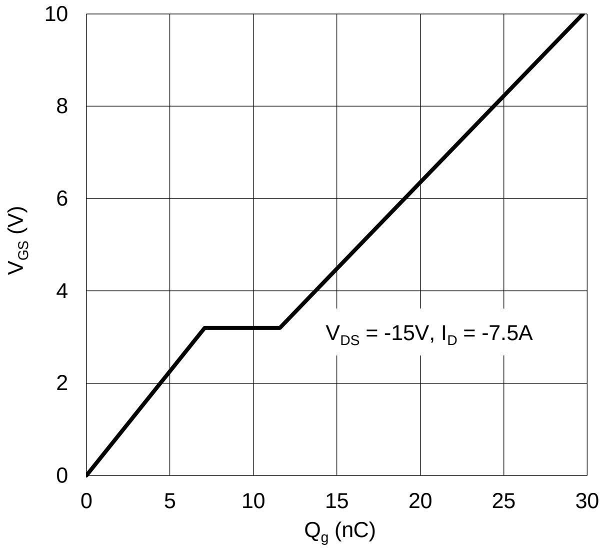


Figure 11. Gate Charge

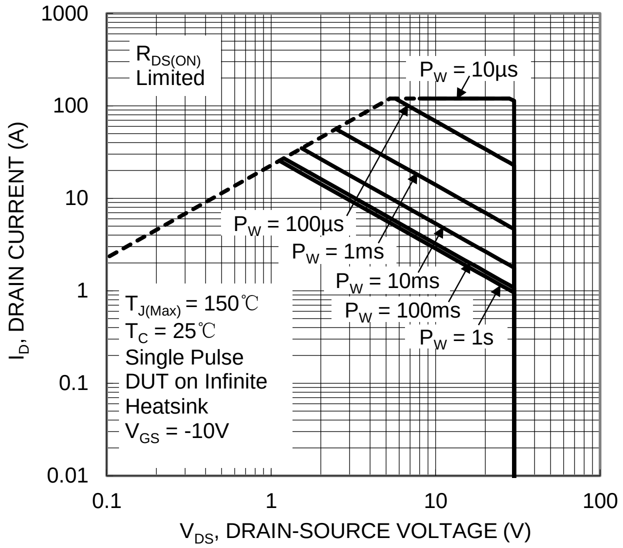


Figure 12. SOA, Safe Operation Area

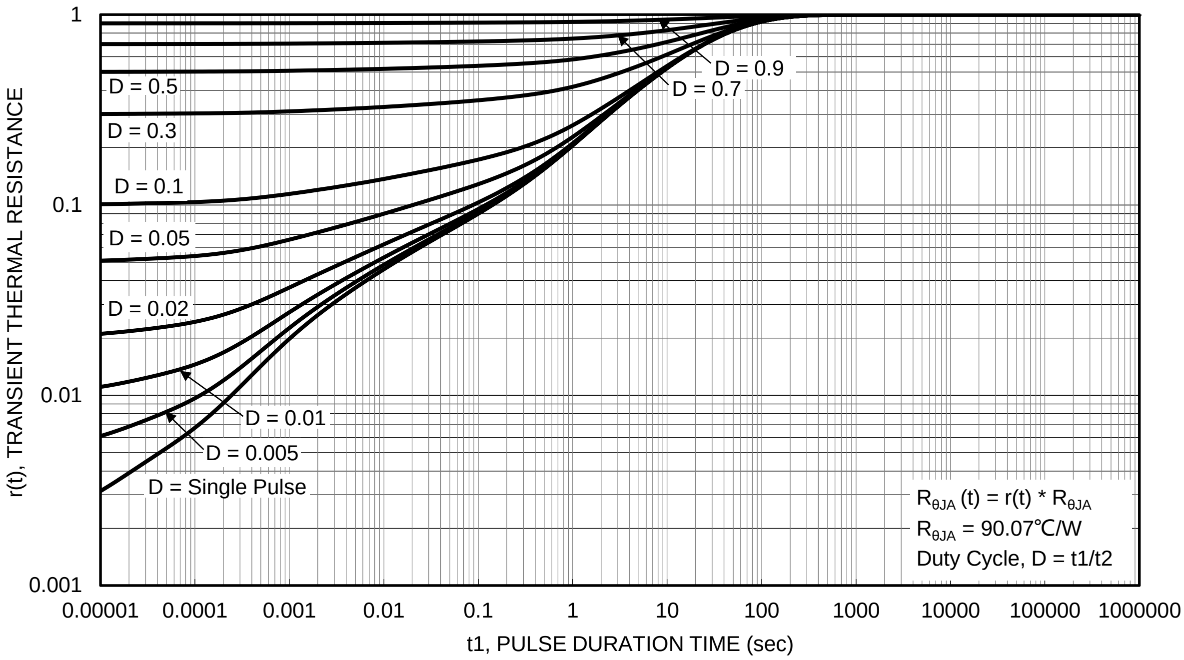
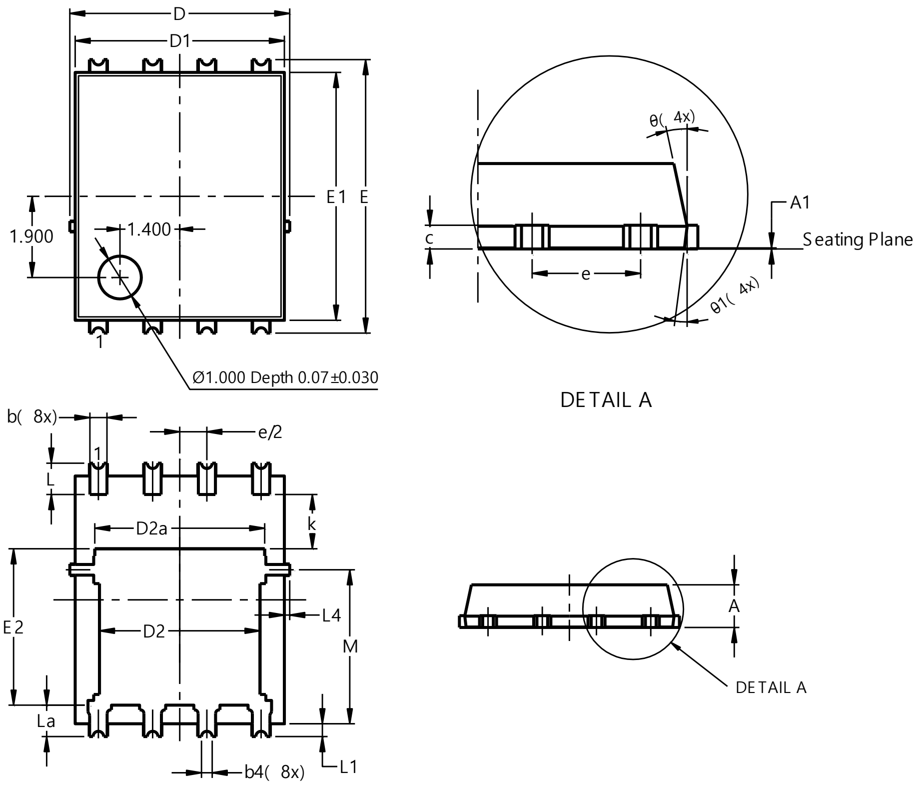


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

PowerDI5060-8 (SWP) (Type UX)



Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

(Table title: **PowerDI5060-8 (SWP) (Type UX)**)

Suggested Pad Layout

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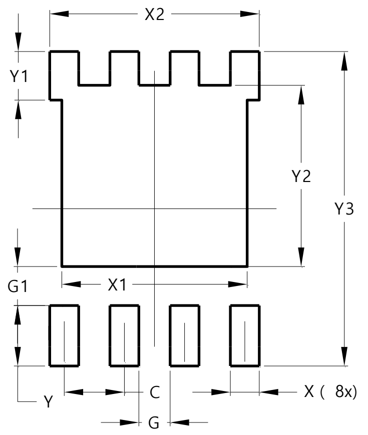

Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610